

# IRLB4030PbF

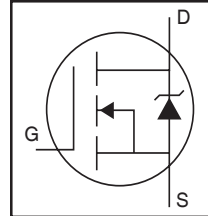
## Applications

- DC Motor Drive
- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits

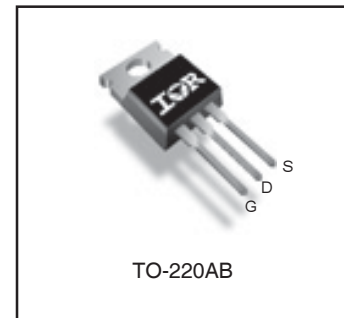
## Benefits

- Optimized for Logic Level Drive
- Very Low  $R_{DS(ON)}$  at 4.5V  $V_{GS}$
- Superior  $R^*Q$  at 4.5V  $V_{GS}$
- Improved Gate, Avalanche and Dynamic  $dV/dt$  Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode  $dV/dt$  and  $dI/dt$  Capability
- Lead-Free

HEXFET® Power MOSFET



$V_{DSS}$		<b>100V</b>
$R_{DS(on)}$ <b>typ.</b>		<b>3.4mΩ</b>
	<b>max.</b>	<b>4.3mΩ</b>
$I_D$		<b>180A</b>



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

## Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	180	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	130	
$I_{DM}$	Pulsed Drain Current ①	730	
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	370	W
	Linear Derating Factor	2.5	W/°C
$V_{GS}$	Gate-to-Source Voltage	± 16	V
$dv/dt$	Peak Diode Recovery ③	21	V/ns
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)	

## Avalanche Characteristics

$E_{AS}$ (Thermally limited)	Single Pulse Avalanche Energy ②	305	mJ
$I_{AR}$	Avalanche Current ①	See Fig. 14, 15, 22a, 22b,	A
$E_{AR}$	Repetitive Avalanche Energy ④		mJ

## Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑧	—	0.40	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient ⑦ ⑧	—	62	

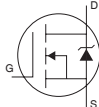
Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.10	—	V/°C	Reference to $25^\circ\text{C}$ , $I_D = 5mA$ ①
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	3.4	4.3	mΩ	$V_{GS} = 10V, I_D = 110A$ ④
		—	3.6	4.5		$V_{GS} = 4.5V, I_D = 92A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 100V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 100V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
$R_{G(int)}$	Internal Gate Resistance	—	2.1	—	Ω	

Dynamic @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
gfs	Forward Transconductance	320	—	—	S	$V_{DS} = 25V, I_D = 110A$
$Q_g$	Total Gate Charge	—	87	130	nC	$I_D = 110A$
$Q_{gs}$	Gate-to-Source Charge	—	27	—		$V_{DS} = 50V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	45	—		$V_{GS} = 4.5V$ ④
$Q_{sync}$	Total Gate Charge Sync. ( $Q_g - Q_{gd}$ )	—	42	—		$I_D = 110A, V_{DS} = 0V, V_{GS} = 4.5V$
$t_{d(on)}$	Turn-On Delay Time	—	74	—	ns	$V_{DD} = 65V$
$t_r$	Rise Time	—	330	—		$I_D = 110A$
$t_{d(off)}$	Turn-Off Delay Time	—	110	—		$R_G = 2.7\Omega$
$t_f$	Fall Time	—	170	—		$V_{GS} = 4.5V$ ④
$C_{iss}$	Input Capacitance	—	11360	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	670	—		$V_{DS} = 50V$
$C_{rss}$	Reverse Transfer Capacitance	—	290	—		$f = 1.0MHz$
$C_{oss\ eff. (ER)}$	Effective Output Capacitance (Energy Related) ⑥	—	760	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 80V$ ⑥
$C_{oss\ eff. (TR)}$	Effective Output Capacitance (Time Related) ⑤	—	1140	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 80V$ ⑤

## Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	180	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	730		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 110A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	50	—	ns	$T_J = 25^\circ\text{C}$ $V_R = 85V,$
		—	60	—		$T_J = 125^\circ\text{C}$ $I_F = 110A$
$Q_{rr}$	Reverse Recovery Charge	—	88	—	nC	$T_J = 25^\circ\text{C}$ $di/dt = 100A/\mu s$ ④
		—	130	—		$T_J = 125^\circ\text{C}$
$I_{RRM}$	Reverse Recovery Current	—	3.3	—	A	$T_J = 25^\circ\text{C}$
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

## Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by  $T_{Jmax}$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.05mH$   
 $R_G = 25\Omega, I_{AS} = 110A, V_{GS} = 10V$ . Part not recommended for use above this value.
- ③  $I_{SD} \leq 110A, di/dt \leq 1330A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$ .
- ④ Pulse width  $\leq 400\mu s$ ; duty cycle  $\leq 2\%$ .
- ⑤  $C_{oss\ eff. (TR)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑥  $C_{oss\ eff. (ER)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note # AN-994 techniques refer to application note #AN-994.
- ⑧  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$ .

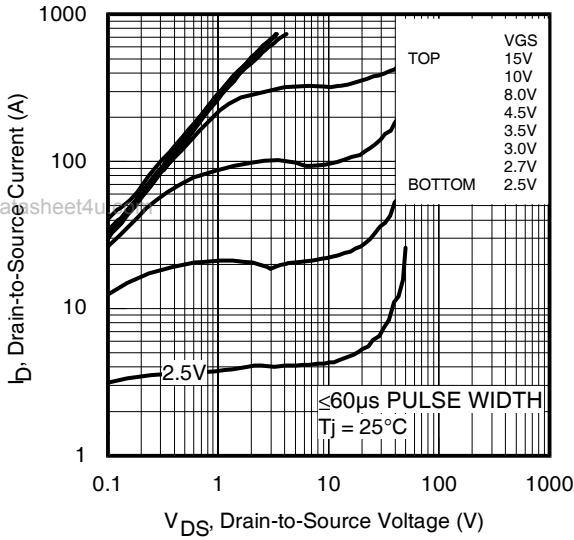


Fig 1. Typical Output Characteristics

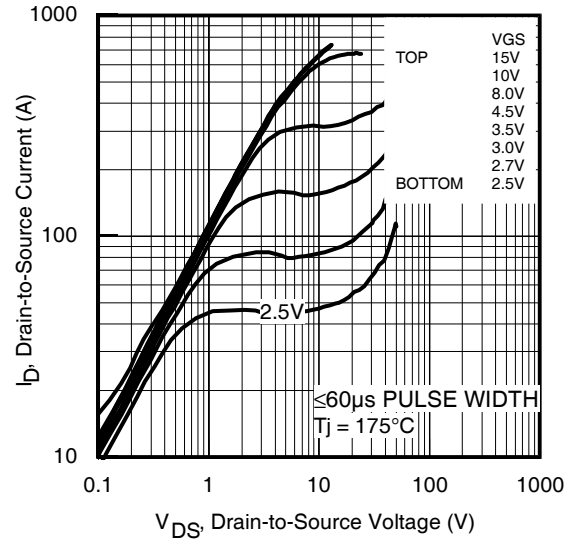


Fig 2. Typical Output Characteristics

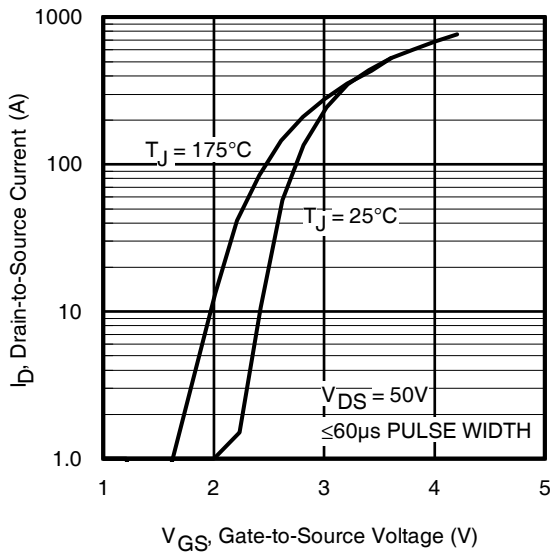


Fig 3. Typical Transfer Characteristics

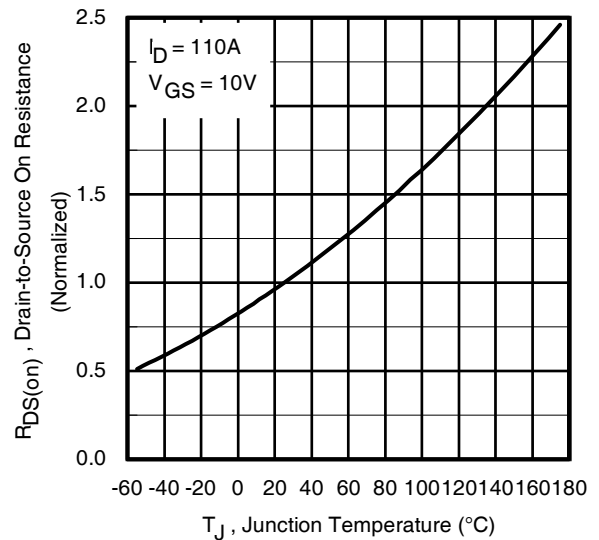


Fig 4. Normalized On-Resistance vs. Temperature

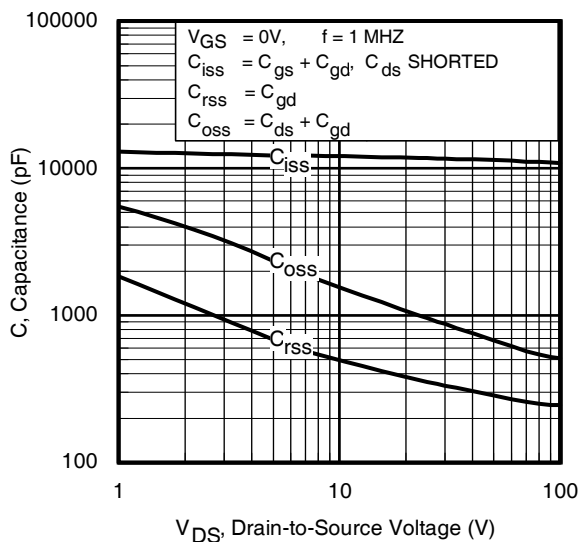


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

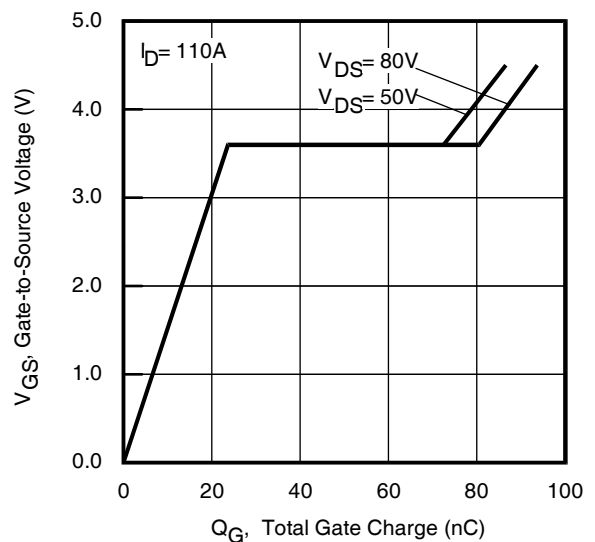
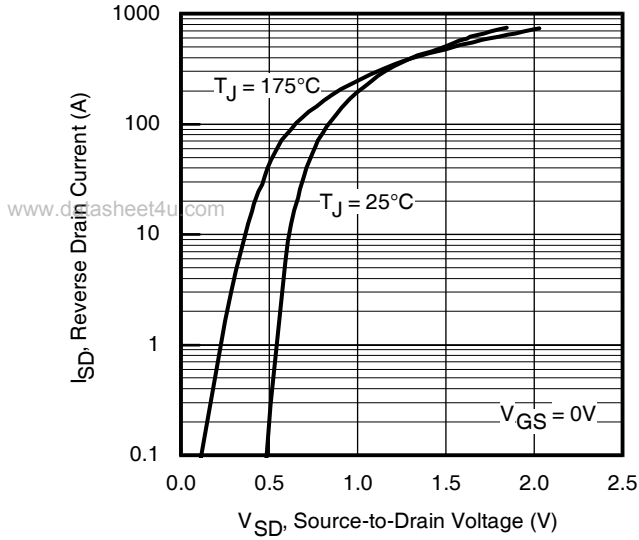
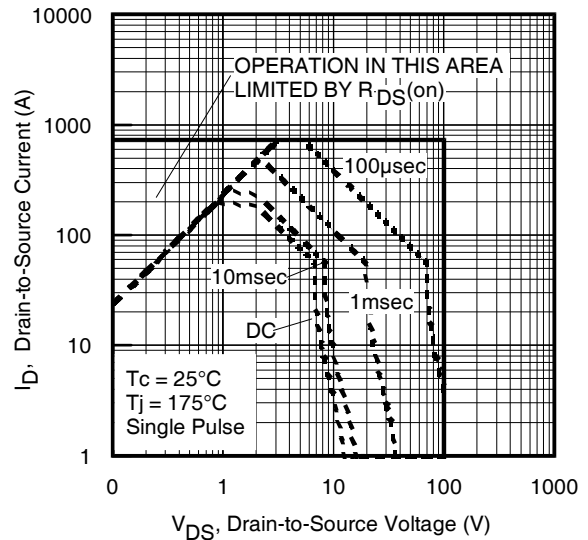


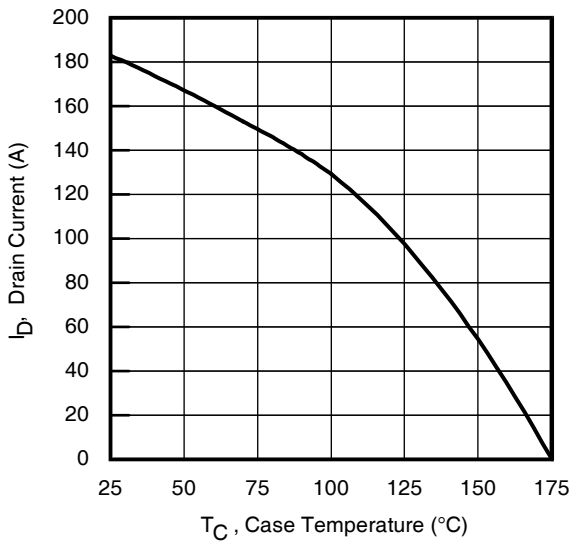
Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage



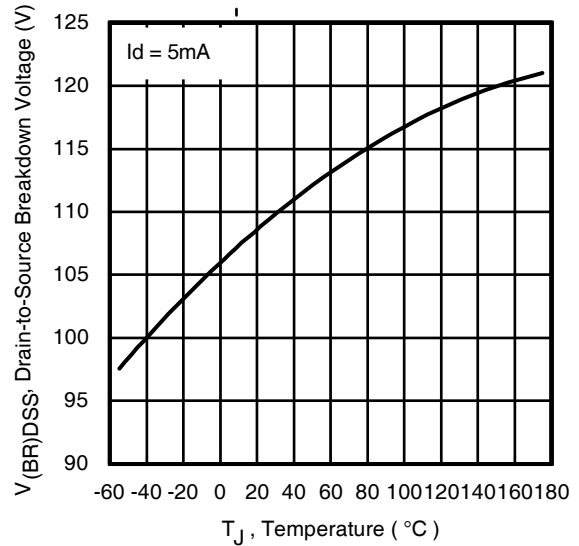
**Fig 7.** Typical Source-Drain Diode Forward Voltage



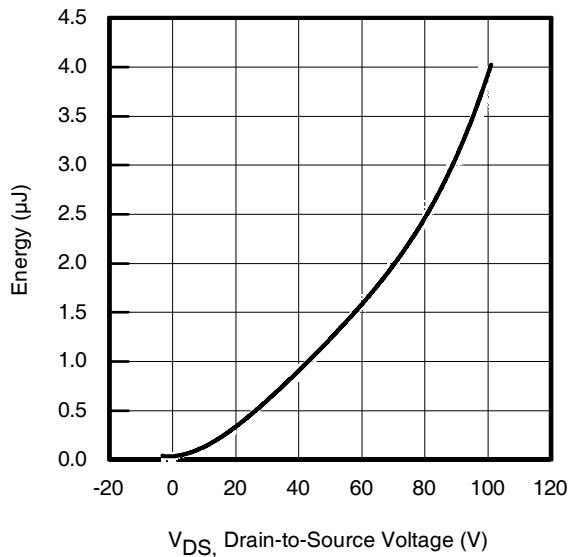
**Fig 8.** Maximum Safe Operating Area



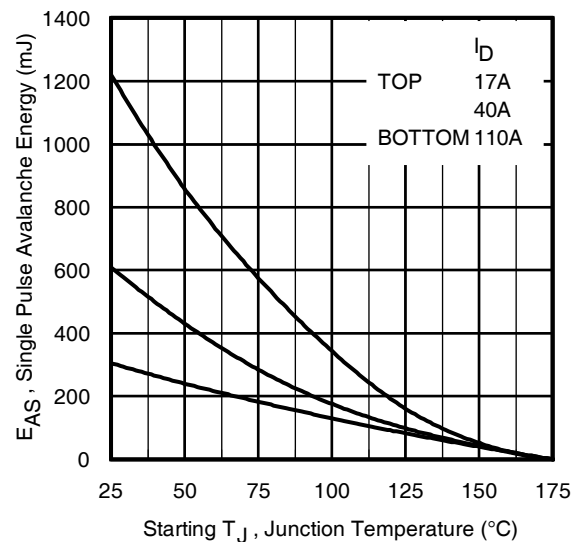
**Fig 9.** Maximum Drain Current vs. Case Temperature



**Fig 10.** Drain-to-Source Breakdown Voltage



**Fig 11.** Typical  $C_{OSS}$  Stored Energy



**Fig 12.** Maximum Avalanche Energy vs. Drain Current

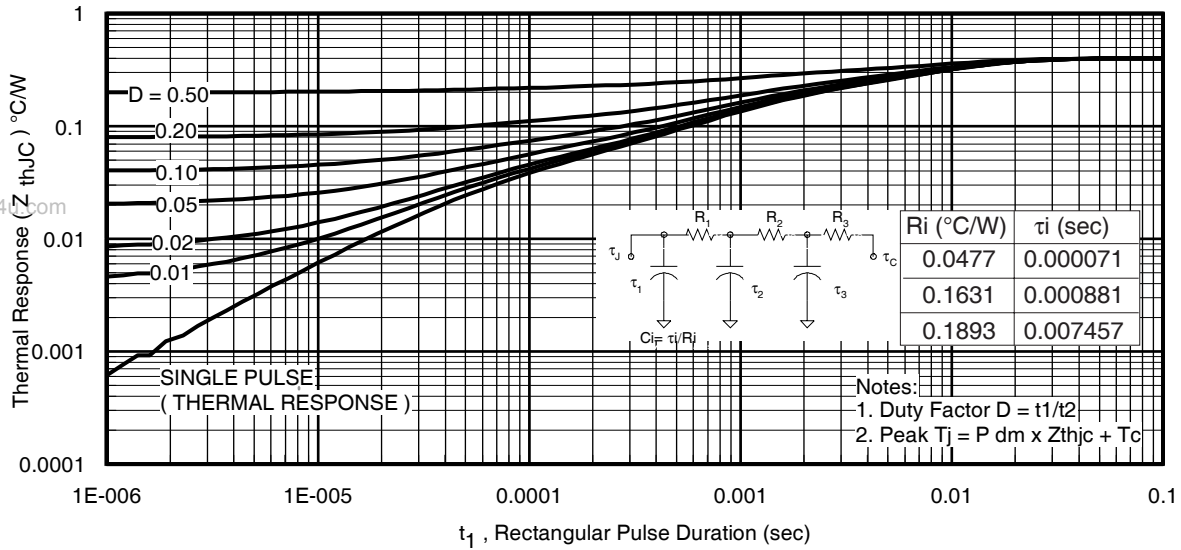


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

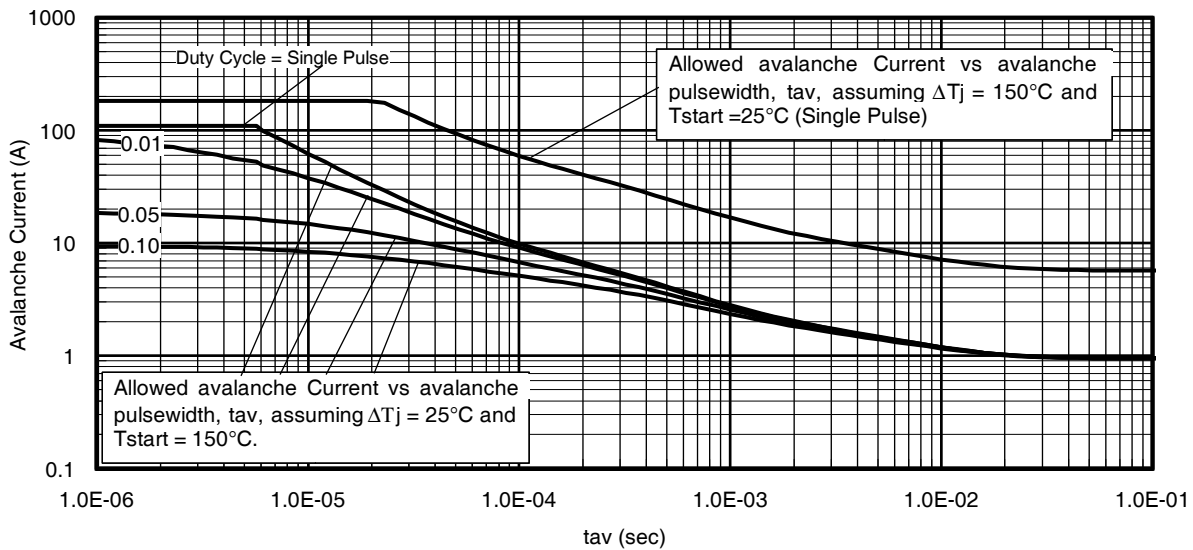


Fig 14. Typical Avalanche Current vs. Pulsewidth

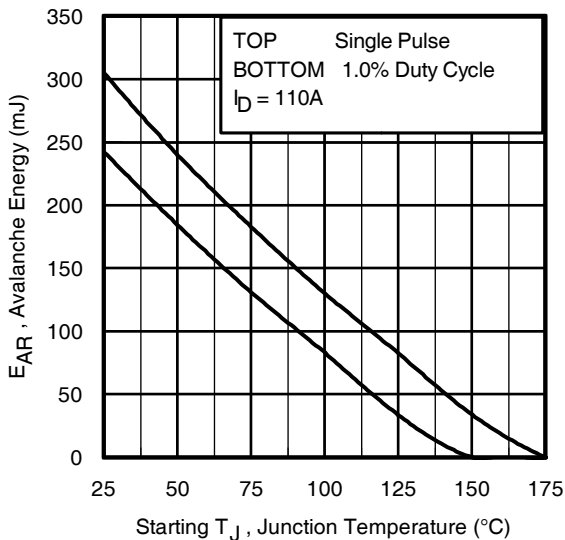


Fig 15. Maximum Avalanche Energy vs. Temperature

**Notes on Repetitive Avalanche Curves , Figures 14, 15:**  
(For further info, see AN-1005 at [www.irf.com](http://www.irf.com))

1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 16a, 16b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 14, 15).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see Figures 13)

$$P_{D(ave)} = 1/2 ( 1.3 \cdot BV \cdot I_{av} ) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

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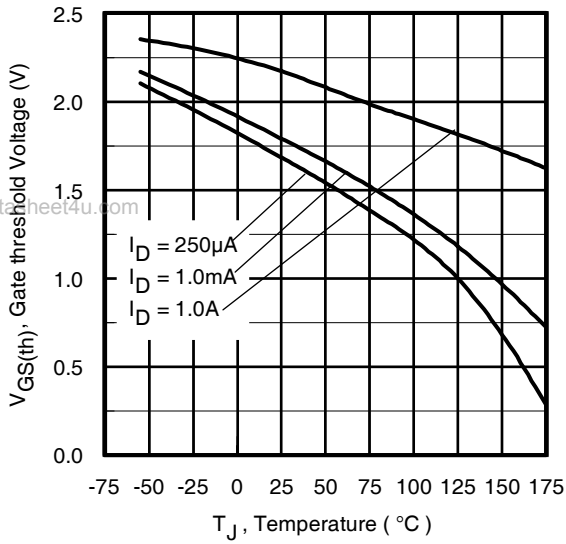


Fig 16. Threshold Voltage vs. Temperature

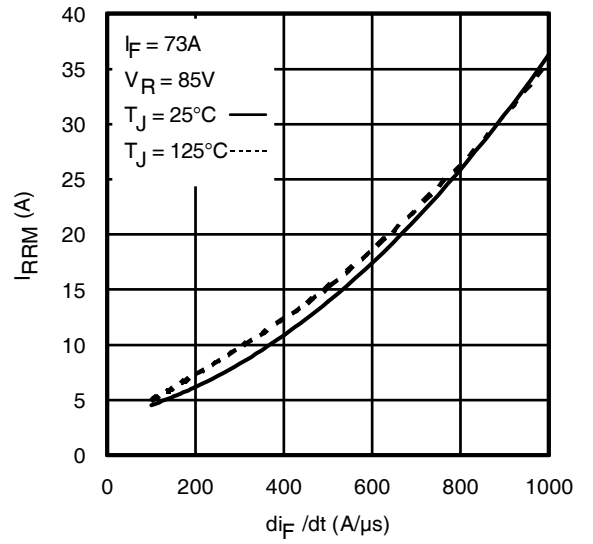


Fig. 17 - Typical Recovery Current vs.  $di_T/dt$

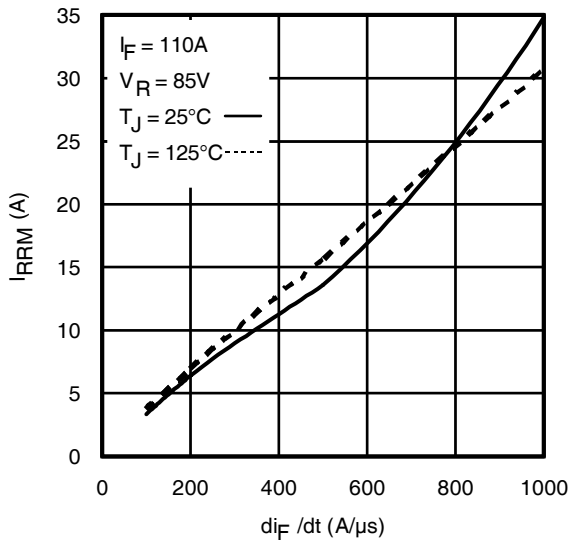


Fig. 18 - Typical Recovery Current vs.  $di_T/dt$

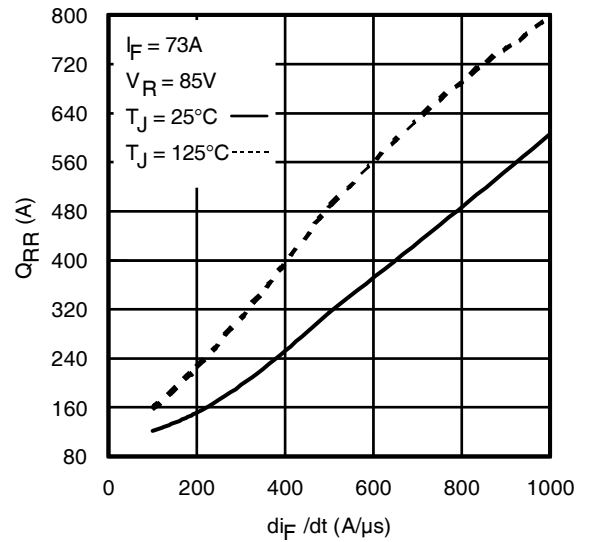


Fig. 19 - Typical Stored Charge vs.  $di_T/dt$

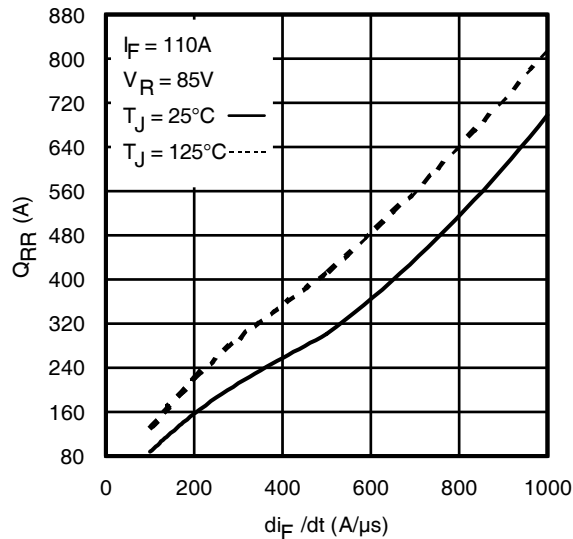
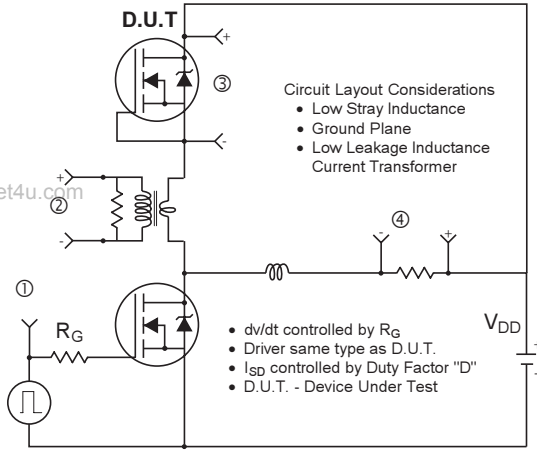
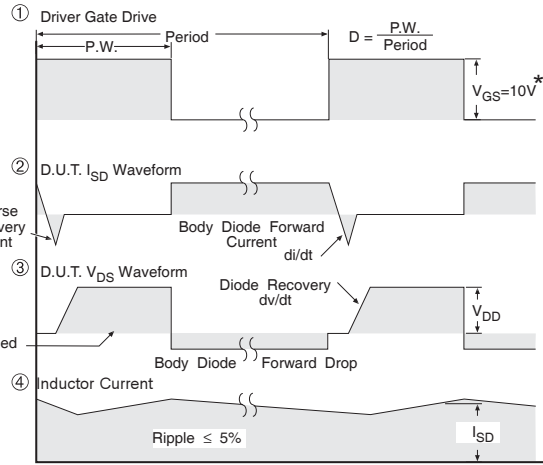


Fig. 20 - Typical Stored Charge vs.  $di_T/dt$

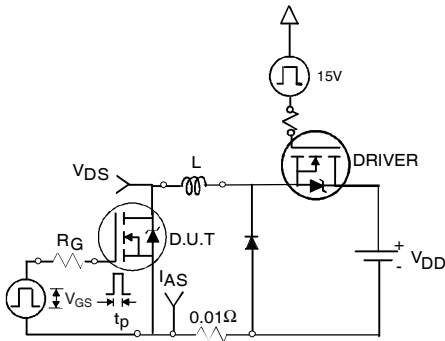
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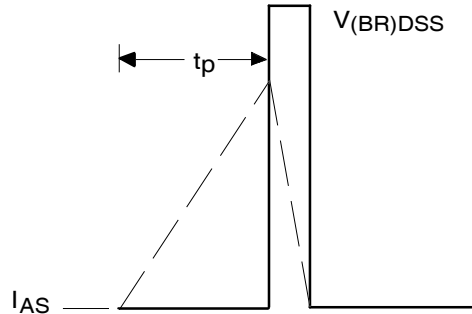
**Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs**



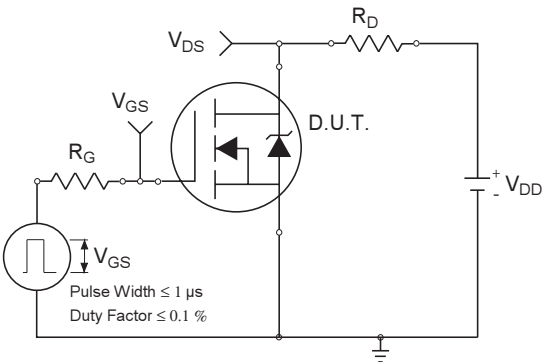
\*  $V_{GS} = 5V$  for Logic Level Devices



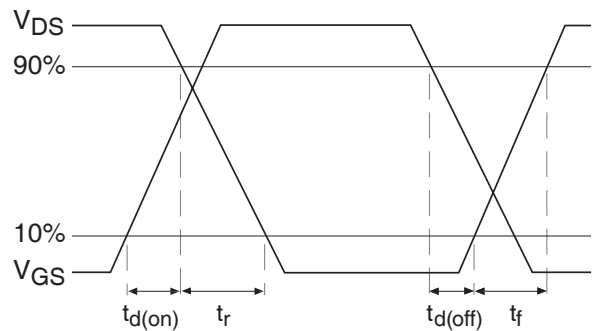
**Fig 22a. Unclamped Inductive Test Circuit**



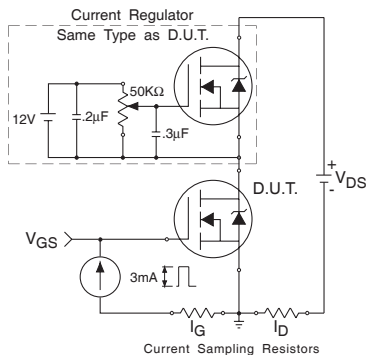
**Fig 22b. Unclamped Inductive Waveforms**



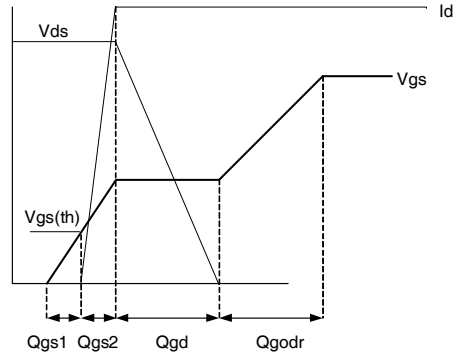
**Fig 23a. Switching Time Test Circuit**



**Fig 23b. Switching Time Waveforms**



**Fig 24a. Gate Charge Test Circuit**



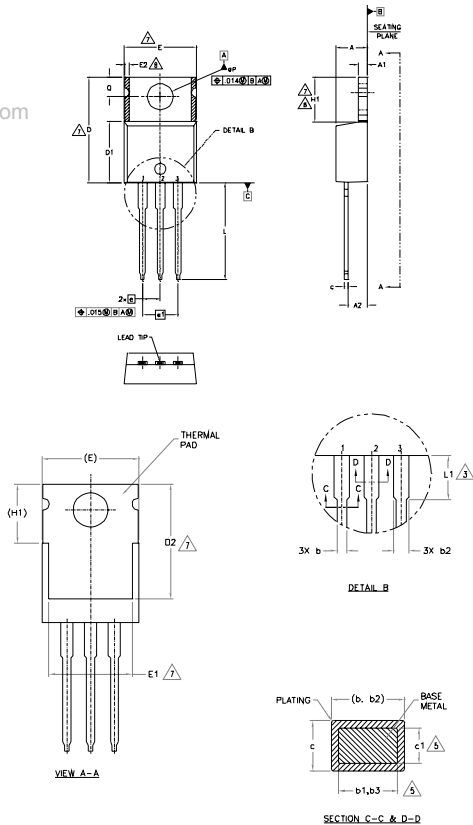
**Fig 24b. Gate Charge Waveforms**

# IRLB4030PbF

## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)

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- NOTES:
- 1.- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
  - 2.- DIMENSIONS ARE SHOWN IN INCHES (MILLIMETERS)
  - 3.- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
  - 4.- DIMENSION G, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
  - 5.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
  - 6.- CONTROLLING DIMENSION - INCHES.
  - 7.- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
  - 8.- DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
  - 9.- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC		.100 BSC		
e1	5.08 BSC		.200 BSC		
H1	5.84	6.66	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	3.66	4.06	.140	.160	3
øP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

**LEAD ASSIGNMENTS**

- ISSEFET  
1.- GATE  
2.- DRAIN  
3.- SOURCE

**ISBTA, CUPACK**

- 1.- GATE  
2.- COLLECTOR  
3.- EMITTER

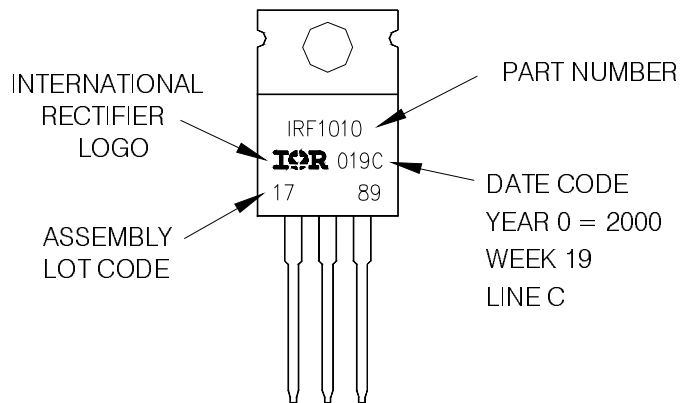
**DIODES**

- 1.- ANODE  
2.- CATHODE  
3.- ANODE

## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
LOT CODE 1789  
ASSEMBLED ON WW 19, 2000  
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead - Free"



TO-220AB packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Industrial market.  
Qualification Standards can be found on IR's Web site.